ABSTRACT

When an SOI wafer is produced by using a bond wafer made of silicon single crystal to form an SOI layer and a base wafer made of silicon single crystal to be a support substrate, one silicon wafer selected from a group consisting of an epitaxial wafer, an FZ wafer, a nitrogen doped wafer, a hydrogen annealed wafer, an intrinsic gettering wafer, a nitrogen doped and annealed wafer, and an entire N-region wafer is used as the bond wafer. Thereby, even where a thin insulator film or a thin SOI layer is formed in the SOI wafer, COPs are hardly detected in inspection of the SOI layer after the SOI wafer was completed, and a high quality SOI wafer is provided.